

# STPS660CB(-TR)

# POWER SCHOTTKY RECTIFIER

#### **MAIN PRODUCT CHARACTERISTICS**

I <sub>F(AV)</sub>	2 x 3 A	
V <sub>RRM</sub>	60 V	
V <sub>F</sub> (max)	0.59 V	

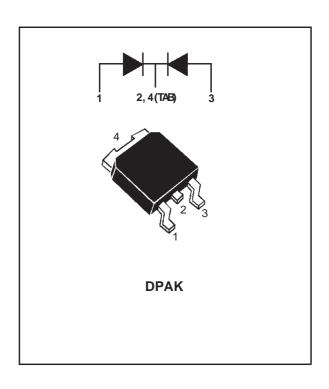
#### **FEATURES AND BENEFITS**

- NEGLIGIBLE SWITCHING LOSSES
- LOW FORWARD DROP VOLTAGE
- LOW CAPACITANCE
- HIGH REVERSE AVALANCHE SURGE CAPABILITY
- TAPE AND REEL OPTION: -TR

#### **DESCRIPTION**

High voltage dual Schottky rectifier suited to Switch Mode Power Supplies and other Power Converters.

Packaged in DPAK, this device is intended for use in medium voltage operation, and particularly, in high frequency circuitries where low switching losses are required.



## **ABSOLUTE RATINGS (limiting values)**

Symbol	Parameter	Value	Unit	
$V_{RRM}$	Repetitive peak reverse voltage	60	V	
I <sub>F(RMS)</sub>	RMS forward current	6	А	
I <sub>F(AV)</sub>	Average forward current	Tcase = 120℃ δ = 0.5	3	А
I <sub>FSM</sub>	Surge non repetitive forward current	tp = 10 ms Sinusoidal	50	А
I <sub>RRM</sub>	Repetitive peak reverse current	tp = 2 μs F = 1kHz	1	А
T <sub>stg</sub>	Storage temperature range		- 65 to + 150	°C
Tj	Maximum junction temperature	125		
dV/dt	Critical rate of rise of reverse voltage	10000	V/µs	

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## THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
R <sub>th(j-c)</sub>	Junction to case	Per diode	3.5	°C/W
		Total	2	

## STATIC ELECTRICAL CHARACTERISTICS

Symbol	Tests Conditions	Tests Co	Min.	Тур.	Max.	Unit	
I <sub>R</sub> *	Reverse leakage current	Tj = 25°C	V <sub>R</sub> = 60 V			30	μΑ
		Tj = 125°C			2.5	10	mA
V <sub>F</sub> **	Forward voltage drop	Tj = 25°C	I <sub>F</sub> = 3 A			0.65	V
		Tj = 125°C	I <sub>F</sub> = 3 A		0.55	0.59	

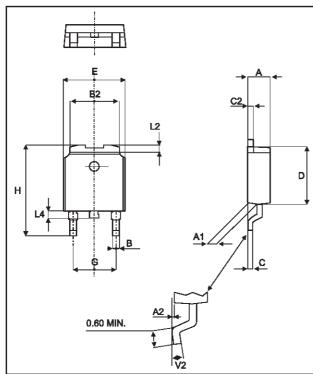
To evaluate the maximum conduction losses use the following equation :

 $P = 0.49 \text{ x } I_{F(AV)} + 0.035 I_{F}^{2}_{(RMS)}$ 

Typical junction capacitance,  $V_R = 0 \text{ V}$  F = 1 MHz  $Tj = 25^{\circ}\text{C}$  C = 815 pF

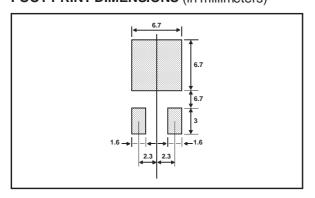
### **PACKAGE MECHANICAL DATA**

**DPAK** 



	DIMENSIONS					
REF.	Millimeters			Inches		
	Min.	Тур.	Max	Min.	Тур.	Max.
Α	2.20		2.40	0.086		0.094
A1	0.90		1.10	0.035		0.043
A2	0.03		0.23	0.001		0.009
В	0.64		0.90	0.025		0.035
B2	5.20		5.40	0.204		0.212
С	0.45		0.60	0.017		0.023
C2	0.48		0.60	0.018		0.023
D	6.00		6.20	0.236		0.244
Е	6.40		6.60	0.251		0.259
G	4.40		4.60	0.173		0.181
Н	9.35		10.10	0.368		0.397
L2		0.80			0.031	
L4	0.60		1.00	0.023		0.039
V2	0°		8°	0°		8°

## FOOT PRINT DIMENSIONS (in millimeters)



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